

## P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
- 60	0.340 at V <sub>GS</sub> = - 10 V	- 1.25
	0.550 at V <sub>GS</sub> = - 4.5 V	- 1

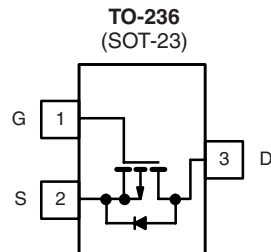
### FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET



**RoHS\***  
COMPLIANT

HALOGEN  
**FREE**  
Available



Top View  
Si2309DS (A9)\*  
\* Marking Code

**Ordering Information:** Si2309DS-T1  
Si2309DS-T1-E3 (Lead (Pb)-free)  
Si2309DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 1.25	A
	T <sub>A</sub> = 70 °C		- 0.85	
Pulsed Drain Current		I <sub>DM</sub>	- 8	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 5	
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.25	W
	T <sub>A</sub> = 70 °C		0.8	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	R <sub>thJA</sub>		100	°C/W
	Steady State		130	166	
Maximum Junction-to-Lead <sup>a</sup>	Steady State	R <sub>thJL</sub>	45	60	

Notes:

a. Surface Mounted on FR4 board.

b. t ≤ 5 s.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



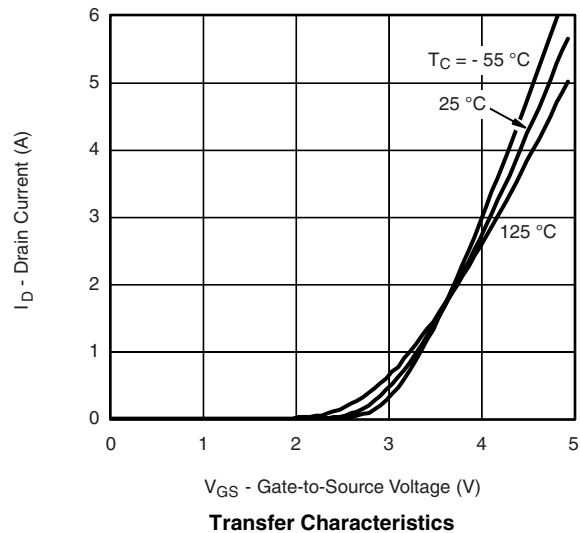
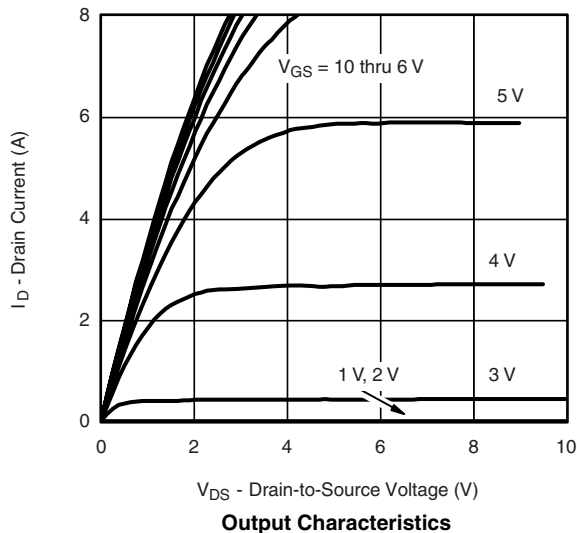
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1			
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			-50	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq -4.5\text{ V}, V_{GS} = -10\text{ V}$	-6			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -1.25\text{ A}$		0.275	0.340	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		0.406	0.550	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -4.5\text{ V}, I_D = -1\text{ A}$		1.9		S
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -1.25\text{ A}$		5.4	12	nC
Gate-Source Charge	$Q_{gs}$			1.15		
Gate-Drain Charge	$Q_{gd}$			0.92		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		10.5	20	ns
Rise Time	$t_r$			11.5	20	
Turn-Off Delay Time	$t_{d(off)}$			15.5	30	
Fall Time	$t_f$			7.5	15	
<b>Source-Drain Rating Characteristics<sup>b</sup></b>						
Continuous Current	$I_S$				-1.25	A
Pulsed Current	$I_{SM}$				-8	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.25\text{ A}, V_{GS} = 0\text{ V}$		-0.82	-1.2	V
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -1.25\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		30	55	ns

**Notes:**

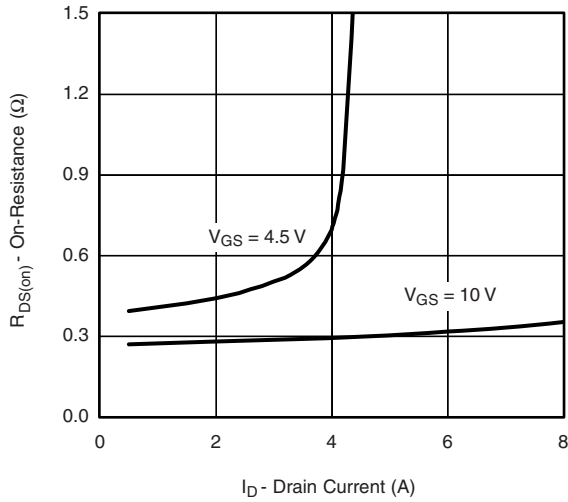
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

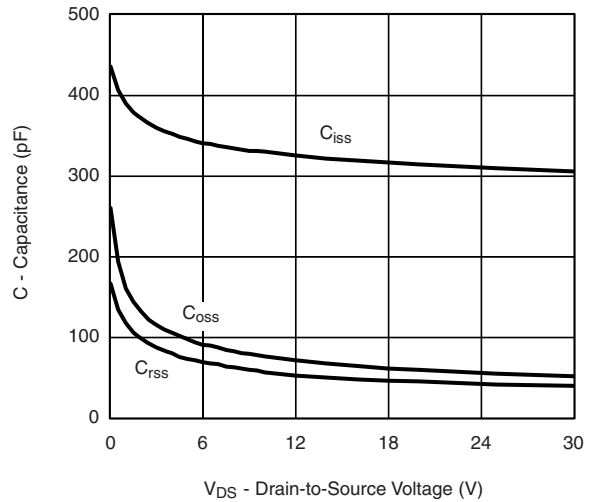
**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted



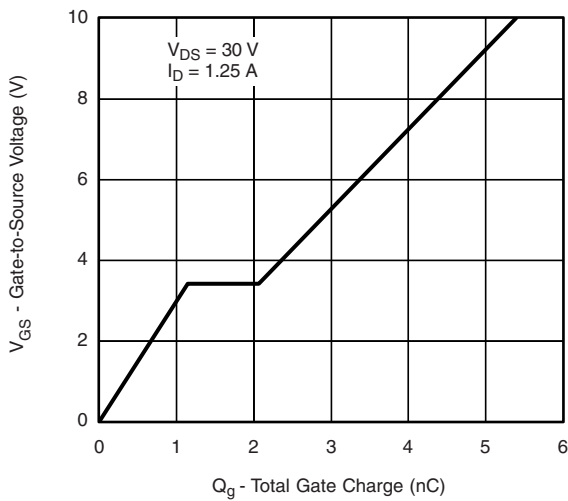
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



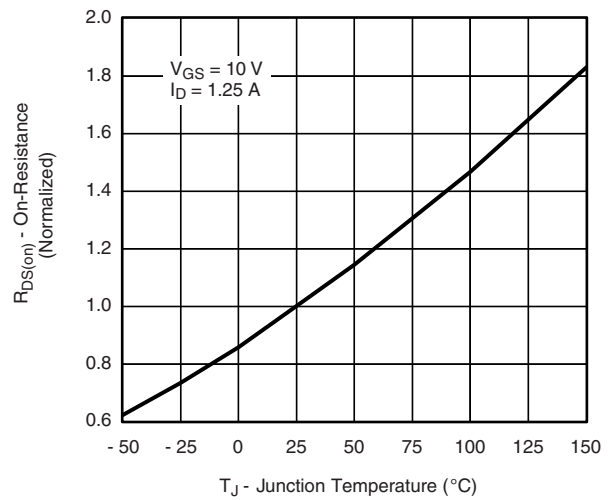
**On-Resistance vs. Drain Current**



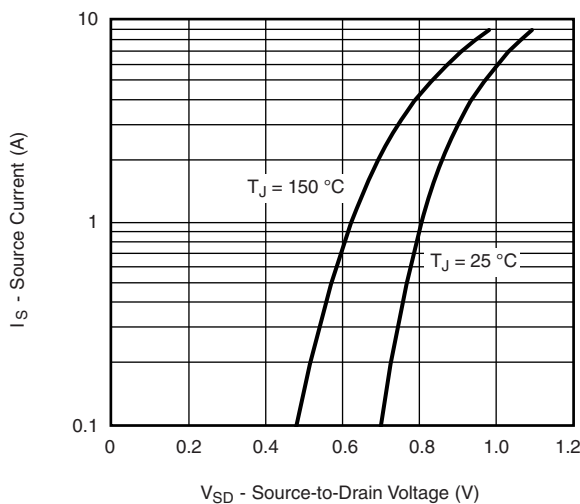
**Capacitance**



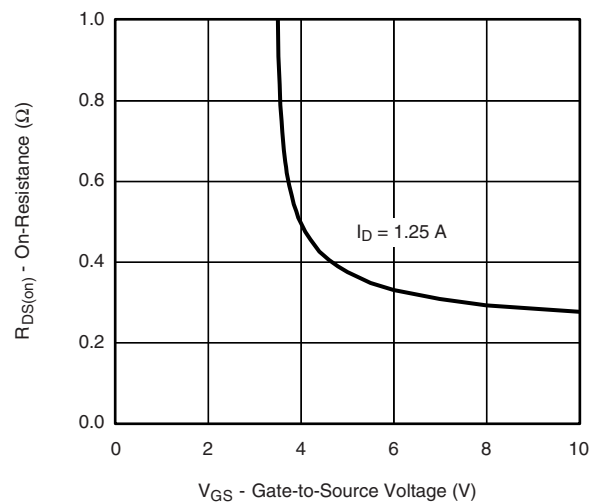
**Gate Charge**



**On-Resistance vs. Junction Temperature**

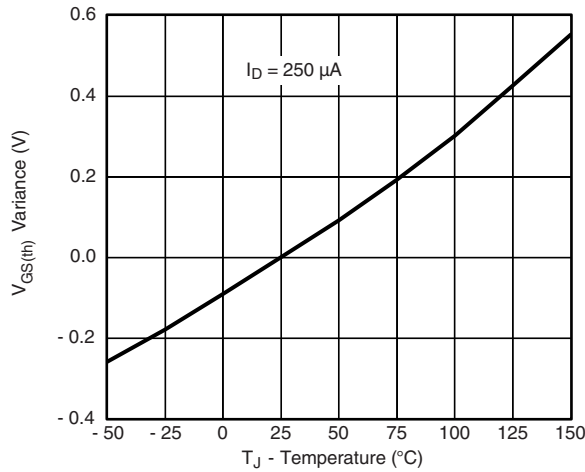


**Source-Drain Diode Forward Voltage**

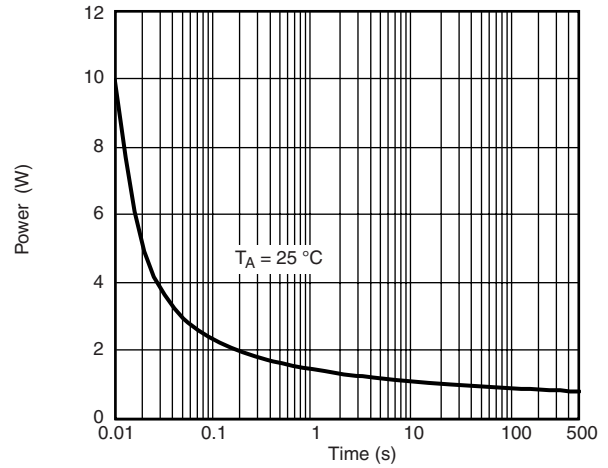


**On-Resistance vs. Gate-to-Source Voltage**

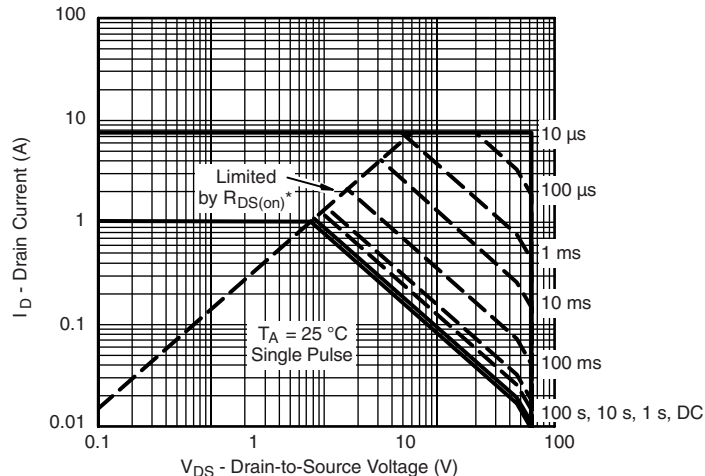
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



**Threshold Voltage**

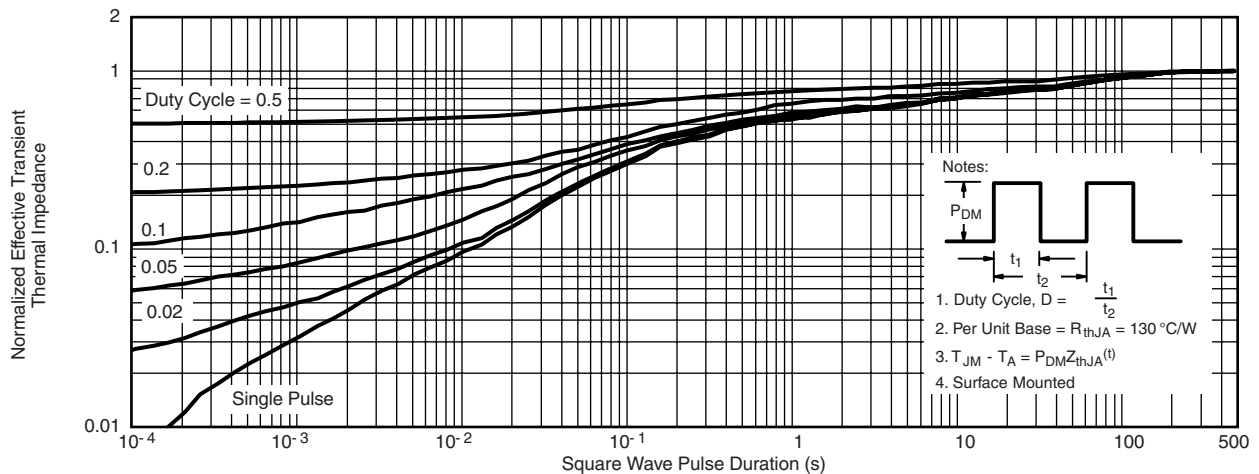


**Single Pulse Power**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Ambient**



Notes:

1. Duty Cycle,  $D = \frac{t_1}{t_2}$
2. Per Unit Base =  $R_{thJA} = 130 \text{ }^\circ\text{C/W}$
3.  $T_{JM} - T_A = P_{DM} Z_{thJA}(t)$
4. Surface Mounted

**Normalized Thermal Transient Impedance, Junction-to-Ambient**

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